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Deep level transient spectroscopy characterization of porous GaP layers

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Photocurrent relaxation in pure and Pr-doped a-As₂S₃ films

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Formation of a double electric layer at the ZnIn₂Sm_{m+3} (m = 1,2,3) - H₂O(S₂-/S₂₂-) interface

Țiuleanu Ion, Simășchevici Alexei, Sprincean Ala

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Mecanisms of photoconductivity decay in bulk and porous InP

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